

# MCR8NG

## Silicon Controlled Rectifiers

### Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

#### Features

- Blocking Voltage of 600 thru 800 Volts
- On-State Current Rating of 8 Amperes RMS at 80°C
- High Surge Current Capability – 80 Amperes
- Rugged, Economical TO-220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- High Immunity to  $dv/dt$  – 100 V/ $\mu$ sec Minimum at 125°C
- These are Pb-Free Devices\*

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) ( $T_J = -40$ to $125^\circ\text{C}$ , Sine Wave, 50 to 60 Hz, Gate Open) MCR8MG MCR8NG	$V_{\text{DRM}}$ , $V_{\text{RRM}}$	600 800	V
On-State RMS Current (180° Conduction Angles; $T_C = 80^\circ\text{C}$ )	$I_{\text{T(RMS)}}$	8.0	A
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, $T_C = 125^\circ\text{C}$ )	$I_{\text{TSM}}$	80	A
Circuit Fusing Consideration ( $t = 8.33$ ms)	$I^2t$	26.5	$\text{A}^2\text{sec}$
Forward Peak Gate Power (Pulse Width $\leq 1.0$ $\mu$ s, $T_C = 80^\circ\text{C}$ )	$P_{\text{GM}}$	5.0	W
Forward Average Gate Power ( $t = 8.3$ ms, $T_C = 80^\circ\text{C}$ )	$P_{\text{G(AV)}}$	0.5	W
Forward Peak Gate Current (Pulse Width $\leq 1.0$ $\mu$ s, $T_C = 80^\circ\text{C}$ )	$I_{\text{GM}}$	2.0	A
Operating Junction Temperature Range	$T_J$	-40 to 125	$^\circ\text{C}$
Storage Temperature Range	$T_{\text{stg}}$	-40 to 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $V_{\text{DRM}}$  and  $V_{\text{RRM}}$  for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



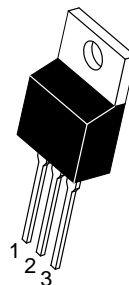
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

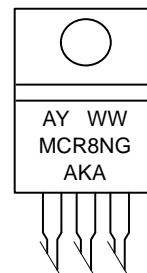
SCRs  
8 AMPERES RMS  
600 thru 800 VOLTS



#### MARKING DIAGRAM



TO-220AB  
CASE 221A-09  
STYLE 3



A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package  
AKA = Diode Polarity

#### PIN ASSIGNMENT

	PIN ASSIGNMENT
1	Cathode
2	Anode
3	Gate
4	Anode

#### ORDERING INFORMATION

Device	Package	Shipping
MCR8NG	TO-220AB (Pb-Free)	50 Units / Rail

# MCR8NG

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	2.2	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient	$R_{\theta JA}$	62.5	
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	$T_L$	260	$^{\circ}\text{C}$

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

### OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current ( $V_D = \text{Rated } V_{DRM}$ and $V_{RRM}$ ; Gate Open)	$I_{DRM}$ , $I_{RRM}$	–	–	0.01	mA
$T_J = 125^{\circ}\text{C}$		–	–	2.0	

### ON CHARACTERISTICS

Peak Forward On-State Voltage (Note ) ( $I_{TM} = 16 \text{ A}$ )	$V_{TM}$	–	–	1.8	V
Gate Trigger Current (Continuous dc) ( $V_D = 12 \text{ V}$ ; $R_L = 100 \Omega$ )	$I_{GT}$	2.0	7.0	15	mA
Holding Current ( $V_D = 12 \text{ V}$ , Gate Open, Initiating Current = 200 mA)	$I_H$	4.0	17	30	mA
Latch Current ( $V_D = 12 \text{ V}$ , $I_G = 15 \text{ mA}$ )	$I_L$	6.0	20	40	mA
Gate Trigger Voltage (Continuous dc) ( $V_D = 12 \text{ V}$ ; $100 \Omega$ )	$V_{GT}$	0.5	0.65	1.0	V
$T_J = 25^{\circ}\text{C}$					
Gate Non-Trigger Voltage ( $V_D = 12 \text{ V}$ ; $R_L = 100 \Omega$ )	$V_{GD}$	0.2	–	–	V
$T_J = 125^{\circ}\text{C}$					

### DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Off-State Voltage ( $V_D = \text{Rated } V_{DRM}$ , Exponential Waveform, Gate Open, $T_J = 125^{\circ}\text{C}$ )	$dv/dt$	100	250	–	V/ $\mu\text{s}$
Critical Rate of Rise of On-State Current IPK = 50 A, Pw = 40 $\mu\text{sec}$ , $di_G/dt = 1 \text{ A}/\mu\text{sec}$ , $I_{gt} = 50 \text{ mA}$	$di/dt$	–	–	50	A/ $\mu\text{s}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width  $\leq 2.0 \text{ ms}$ , Duty Cycle  $\leq 2\%$ .

# MCR8NG

## Voltage Current Characteristic of SCR

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Off State Forward Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Off State Reverse Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Peak On State Voltage
$I_H$	Holding Current

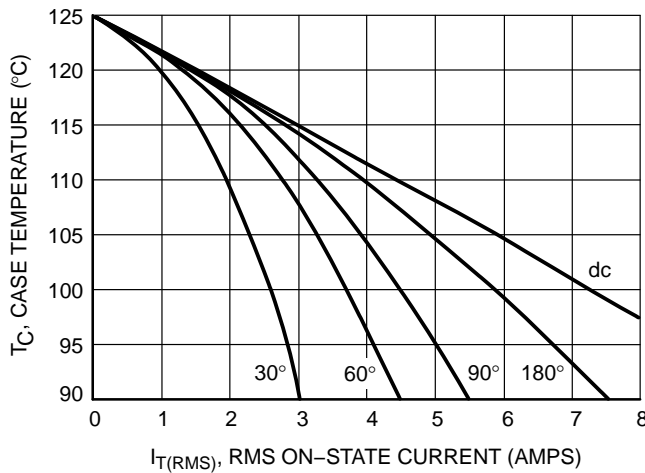
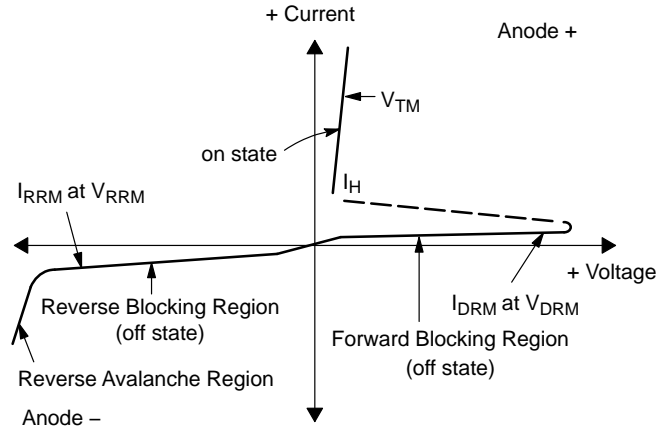


Figure 1. Typical RMS Current Derating

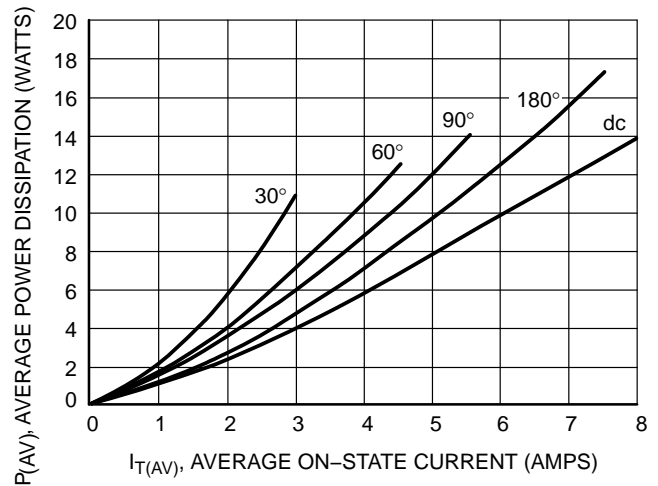


Figure 2. On-State Power Dissipation

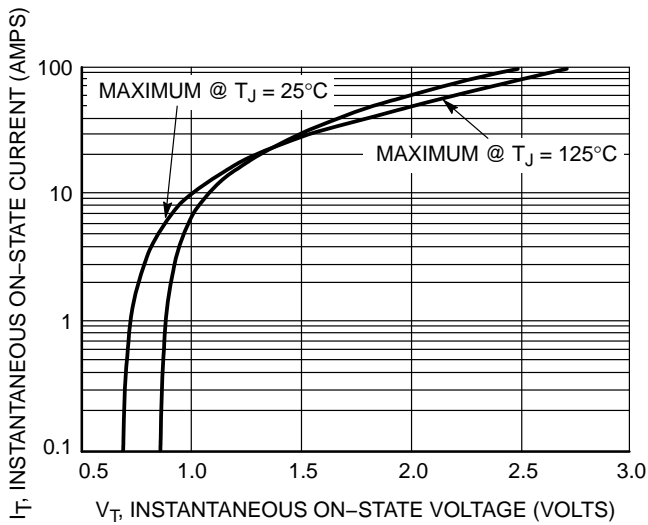


Figure 3. Typical On-State Characteristics

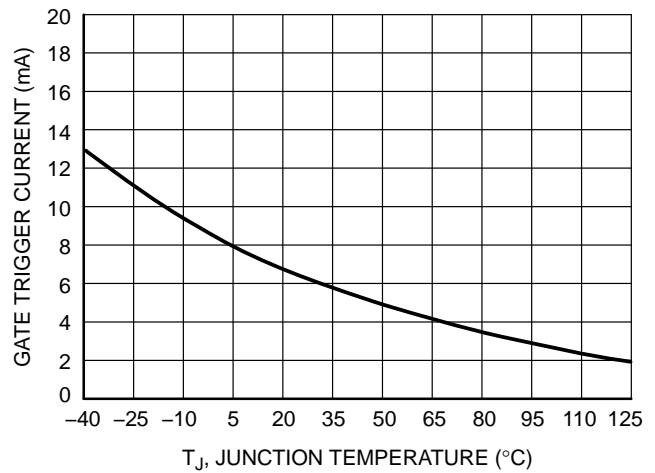
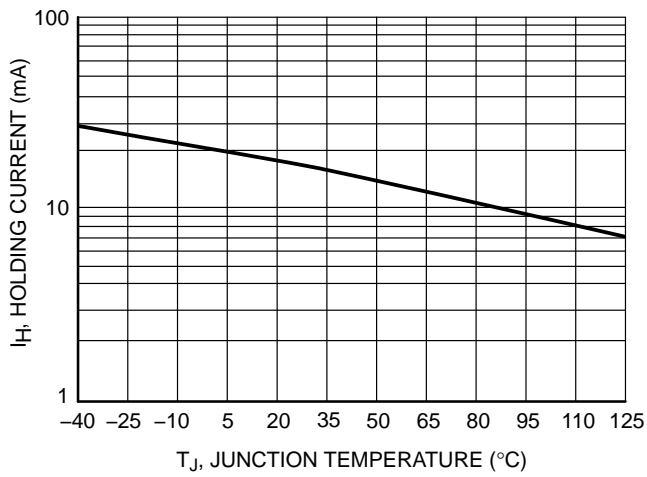
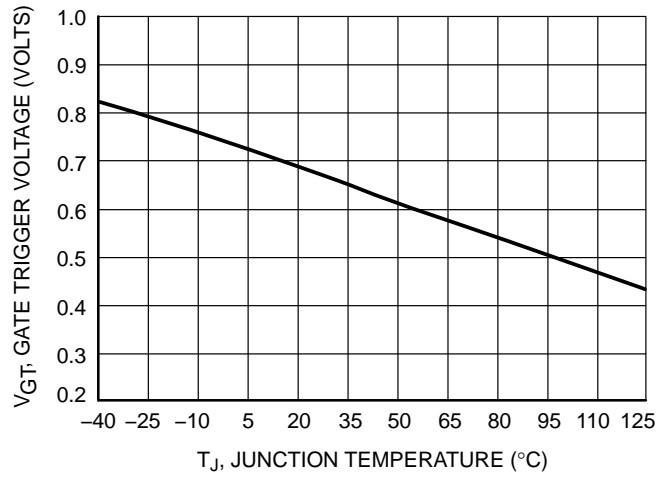


Figure 4. Typical Gate Trigger Current versus Junction Temperature

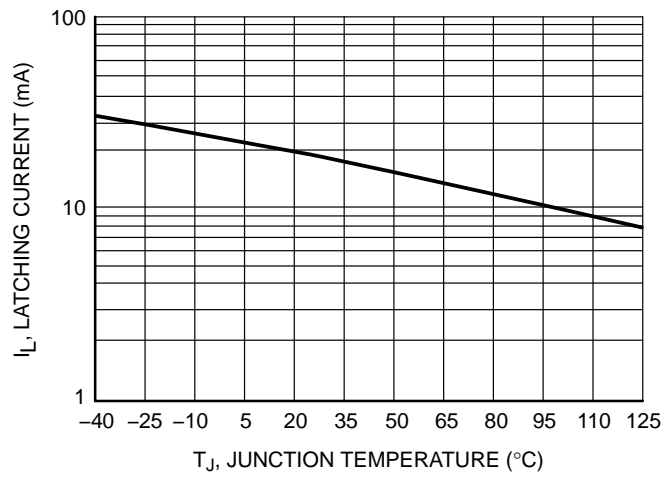
## MCR8NG



**Figure 5. Typical Holding Current versus Junction Temperature**



**Figure 6. Typical Gate Trigger Voltage versus Junction Temperature**

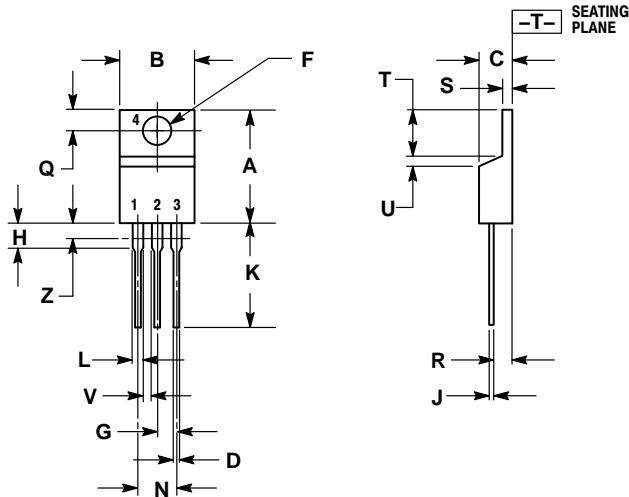


**Figure 7. Typical Latching Current versus Junction Temperature**

# MCR8NG

## PACKAGE DIMENSIONS

TO-220  
CASE 221A-09  
ISSUE AH




### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

### STYLE 3:

- PIN 1: CATHODE  
2. ANODE  
3. GATE  
4. ANODE

ON Semiconductor and the  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
Email: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

N. American Technical Support: 800-282-9855 Toll Free  
USA/Canada  
Europe, Middle East and Africa Technical Support:  
Phone: 421 33 790 2910  
Japan Customer Focus Center  
Phone: 81-3-5817-1050

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative